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## U.S. PATENT DOCUMENTS

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## FOREIGN PATENT DOCUMENTS

	Document Number	Publication Date	Country	Class	Sub Class	Translation Yes or No

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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L.J.U-E	Fayolle, M. et al., "Integration of Cu/SiOC in Dual Damascene interconnect for 0.1µm technology using a new SiC material as dielectric barrier", Proceeding of the IEEE2002 International Interconnect Technology Conference, pp. 39-41, (June 2002).
L.J.U-E	Kim, T.S. et al., "Integration of Organosilicate Glasses (OSGs) In High Performance Copper Interconnects", Advanced Metallization Conference 2001, pp. 25-31, (October 2001)
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Examiner Lynette J. Umeg-Eunini	Date Considered 12/16/2005
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\*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.